

METHOD FOR FORMING AN ONO STRUCTURE IN ONE CHAMBER

ABSTRACT OF THE INVENTION

5

A method for forming an ONO structure in one chamber. The method at least includes the following steps. First of all, a substrate is provided. Then, a first oxide layer is formed on the substrate. Next, a first buffer layer is formed on the first oxide layer, and a silicon nitride layer is formed on the first buffer layer. Next, a second buffer layer is formed on the silicon nitride layer. Finally, a second oxide layer is formed on the second buffer layer.

10

10002978-120501
T0902T 8/62000T